



STV160NF03LAT4 Information



For Reference Only

Part Number STV160NF03LAT4
Manufacturer STMicroelectronics

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 30V 160A POWERSO-10

Package PowerSO-10 Exposed Bottom Pad

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









STV160NF03LAT4 Specifications

Manufacturer Part Number STV160NF03LAT4 Manufacturer STMicroelectronics Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package PowerSO-10 Exposed Bottom Pad Series STripFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 160A (Tc) Drive Voltage (Max Rds On, Min Rds On) 5V, 10V Vgs(th) (Max) @ Id 1V @ 250µA Gate Charge (Qg) (Max) @ Vgs 160nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5350pF @ 25V Vgs (Max) ±15V FET Feature - Power Dissipation (Max) 210W (Tc) Rds On (Max) @ Id, Vgs 3 mOhm @ 80A, 10V Operating Temperature 175°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PowerSO Package / Case PowerSO-10 Exposed Bottom Pad		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package PowerSO-10 Exposed Bottom Pad Series STripFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Ourrent - Continuous Drain (Id) @ 25°C 160A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Iv @ 250µA Gate Charge (Qg) (Max) @ Vgs 160nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5350pF @ 25V Vgs (Max) ±15V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3 mOhm @ 80A, 10V Operating Temperature Mounting Type Surface Mount Supplier Device Package Power SO-10 Exposed Bottom Pad	Manufacturer Part Number	STV160NF03LAT4
Transistors - FETs, MOSFETs - Single Package PowerSO-10 Exposed Bottom Pad Series STripFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 160A (Tc) Drive Voltage (Max Rds On, Min Rds On) 5V, 10V Vgs(th) (Max) @ Id 1V @ 250µA Gate Charge (Qg) (Max) @ Vgs 160nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5350pF @ 25V Vgs (Max) ±15V FET Feature - Power Dissipation (Max) 210W (Tc) Rds On (Max) @ Id, Vgs 3mOhm @ 80A, 10V Operating Temperature 175°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PowerSO Package / Case Power So-10 Exposed Bottom Pad	Manufacturer	STMicroelectronics
PackagePowerSO-10 Exposed Bottom PadSeriesSTripFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C160A (Tc)Drive Voltage (Max Rds On, Min Rds On)5V, 10VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs160nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5350pF @ 25VVgs (Max)±15VFET Feature-Power Dissipation (Max)210W (Tc)Rds On (Max) @ Id, Vgs3 mOhm @ 80A, 10VOperating Temperature175°C (TJ)Mounting TypeSurface MountSupplier Device Package10-PowerSOPackage / CasePowerSO-10 Exposed Bottom Pad	Category	Discrete Semiconductor Products
Series STripFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Tomin to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 160A (Tc) Drive Voltage (Max Rds On, Min Rds On) 5V, 10V Vgs(th) (Max) @ Id 1V @ 250µA Gate Charge (Qg) (Max) @ Vgs 160nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5350pF @ 25V Vgs (Max) ±15V FET Feature Power Dissipation (Max) 210W (Tc) Rds On (Max) @ Id, Vgs 3mOhm @ 80A, 10V Operating Temperature 175°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PowerSO Package / Case Power SO-10 Exposed Bottom Pad		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C160A (Tc)Drive Voltage (Max Rds On, Min Rds On)5V, 10VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs160nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5350pF @ 25VVgs (Max)±15VFET Feature-Power Dissipation (Max)210W (Tc)Rds On (Max) @ Id, Vgs3 mOhm @ 80A, 10VOperating Temperature175°C (TJ)Mounting TypeSurface MountSupplier Device Package10-PowerSOPackage / CasePowerSO-10 Exposed Bottom Pad	Package	PowerSO-10 Exposed Bottom Pad
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 160A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 1V @ 250μA Gate Charge (Qg) (Max) @ Vgs 160nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3 mOhm @ 80A, 10V Operating Temperature Mounting Type Surface Mount Supplier Device Package PowerSO-10 Exposed Bottom Pad	Series	STripFET?
Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C160A (Tc)Drive Voltage (Max Rds On, Min Rds On)5V, 10VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs160nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5350pF @ 25VVgs (Max)±15VFET Feature-Power Dissipation (Max)210W (Tc)Rds On (Max) @ Id, Vgs3 mOhm @ 80A, 10VOperating Temperature175°C (TJ)Mounting TypeSurface MountSupplier Device Package10-PowerSOPackage / CasePowerSO-10 Exposed Bottom Pad	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Surface Mount Supplier Device Package PowerSO-10 Exposed Bottom Pad	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)5V, 10VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs160nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5350pF @ 25VVgs (Max)±15VFET Feature-Power Dissipation (Max)210W (Tc)Rds On (Max) @ Id, Vgs3 mOhm @ 80A, 10VOperating Temperature175°C (TJ)Mounting TypeSurface MountSupplier Device Package10-PowerSOPackage / CasePowerSO-10 Exposed Bottom Pad	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 160nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5350pF @ 25V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3 mOhm @ 80A, 10V Operating Temperature 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerSO-10 Exposed Bottom Pad	Current - Continuous Drain (Id) @ 25°C	160A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 5350pF @ 25V Vgs (Max) ±15V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3 mOhm @ 80A, 10V Operating Temperature 175°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PowerSO Package / Case PowerSO-10 Exposed Bottom Pad	Drive Voltage (Max Rds On, Min Rds On)	5V, 10V
Input Capacitance (Ciss) (Max) @ Vds 5350pF @ 25V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3 mOhm @ 80A, 10V Operating Temperature 175°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PowerSO Package / Case PowerSO-10 Exposed Bottom Pad	Vgs(th) (Max) @ Id	1V @ 250μA
Vgs (Max) ±15V FET Feature - Power Dissipation (Max) 210W (Tc) Rds On (Max) @ Id, Vgs 3 mOhm @ 80A, 10V Operating Temperature 175°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PowerSO Package / Case PowerSO-10 Exposed Bottom Pad	Gate Charge (Qg) (Max) @ Vgs	160nC @ 10V
FET Feature - Power Dissipation (Max) 210W (Tc) Rds On (Max) @ Id, Vgs 3 mOhm @ 80A, 10V Operating Temperature 175°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PowerSO Package / Case PowerSO-10 Exposed Bottom Pad	Input Capacitance (Ciss) (Max) @ Vds	5350pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3 mOhm @ 80A, 10V Operating Temperature 175°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PowerSO Package / Case PowerSO-10 Exposed Bottom Pad	Vgs (Max)	±15V
Rds On (Max) @ Id, Vgs3 mOhm @ 80A, 10VOperating Temperature175°C (TJ)Mounting TypeSurface MountSupplier Device Package10-PowerSOPackage / CasePowerSO-10 Exposed Bottom Pad	FET Feature	-
Operating Temperature 175°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PowerSO Package / Case PowerSO-10 Exposed Bottom Pad	Power Dissipation (Max)	210W (Tc)
Mounting Type Surface Mount Supplier Device Package 10-PowerSO Package / Case PowerSO-10 Exposed Bottom Pad	Rds On (Max) @ Id, Vgs	3 mOhm @ 80A, 10V
Supplier Device Package 10-PowerSO Package / Case PowerSO-10 Exposed Bottom Pad	Operating Temperature	175°C (TJ)
Package / Case PowerSO-10 Exposed Bottom Pad	Mounting Type	Surface Mount
·	Supplier Device Package	10-PowerSO
Report errors?	Package / Case	PowerSO-10 Exposed Bottom Pad
		Report errors?

STV160NF03LAT4 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

STV160NF03LAT4 Payment Methods





















STV160NF03LAT4 Shipping Methods













If you have any question about STV160NF03LAT4, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com